

**FEATURES**

Complimentary to SS8550

Marking : Y1

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current -Continuous	$I_C$	1500	mA
Collector Power Dissipation	$P_C$	300	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

**SS8050 (NPN)**


ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C=0.1mA, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CB}$	$V_{CB}=40V, I_E=0$			0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CB}=20V, I_E=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=100mA$	120		400	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800mA, I_B=80mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800mA, I_B=80mA$			1.2	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=50mA$ $f=30MHz$	100			MHz

 CLASSIFICATION OF  $h_{FE}$ 

Rank	L	H	J
Range	120-200	200-350	300-400

**SS8050** Typical Characteristics

